

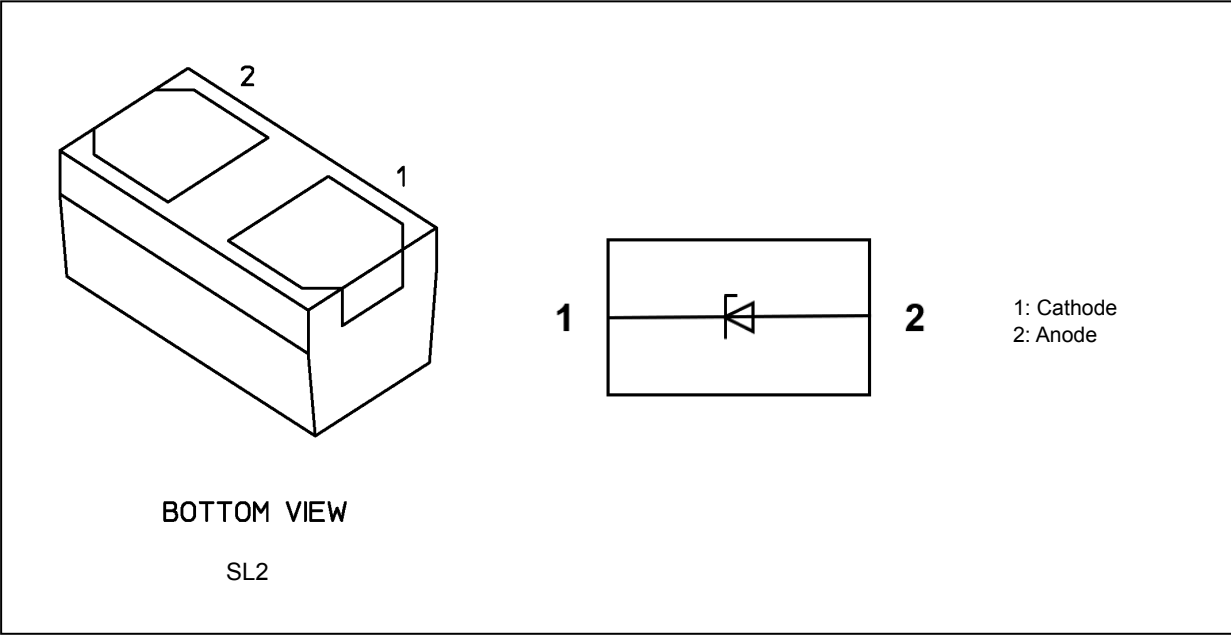
DF2S20ASL

1. Applications

- ESD Protection

Note: This product is designed for protection against electrostatic discharge (ESD) and is not intended for any other purpose, including, but not limited to, voltage regulation.

2. Packaging and Internal Circuit



3. Absolute Maximum Ratings (Note) (Unless otherwise specified, $T_a = 25^{\circ}\text{C}$)

Characteristics	Symbol	Note	Rating	Unit
Electrostatic discharge voltage (IEC61000-4-2) (Contact)	V_{ESD}	(Note 1)	± 12	kV
Electrostatic discharge voltage (IEC61000-4-2) (Air)			± 12	
Peak pulse power ($t_p = 8/20 \mu\text{s}$)	P_{PK}		105	W
Peak pulse current ($t_p = 8/20 \mu\text{s}$)	I_{PP}	(Note 2)	2.5	A
Junction temperature	T_j		150	$^{\circ}\text{C}$
Storage temperature	T_{stg}		-55 to 150	$^{\circ}\text{C}$

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: According to IEC61000-4-2.

Note 2: According to IEC61000-4-5.

Start of commercial production

2022-06

4. Electrical Characteristics (Unless otherwise specified, $T_a = 25^\circ\text{C}$)

V_{RWM} : Working peak reverse voltage
 V_Z : Zener voltage
 V_{BR} : Reverse breakdown voltage
 Z_Z : Dynamic impedance
 I_Z : Zener current
 I_{BR} : Reverse breakdown current
 I_R : Reverse current
 V_R : Reverse voltage
 V_C : Clamp voltage
 I_{PP} : Peak pulse current
 R_{DYN} : Dynamic resistance
 I_F : Forward current
 V_F : Forward voltage

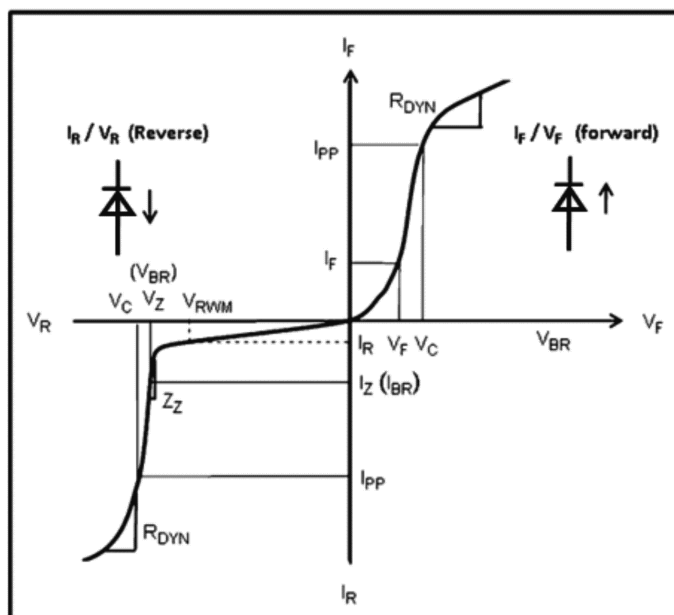


Fig. 4.1 Definitions of Electrical Characteristics

Characteristics	Symbol	Note	Test Condition	Min	Typ.	Max	Unit
Working peak reverse voltage	V_{RWM}		—	—	—	15	V
Zener voltage (Reverse breakdown voltage)	V_Z (V_{BR})		$I_Z = 5\text{ mA}$ ($I_{BR} = 5\text{ mA}$)	18.8	20.0	21.2	V
Dynamic impedance	Z_Z		$I_Z = 5\text{ mA}$ ($I_{BR} = 5\text{ mA}$)	—	—	50	Ω
Reverse current	I_R		$V_{RWM} = 15\text{ V}$	—	—	0.5	μA
Clamp voltage	V_C	(Note 1)	$I_{PP} = 1\text{ A}$	—	26.4	—	V
			$I_{PP} = 2.5\text{ A}$	—	32.6	42	
		(Note 2)	$I_{TLP} = 16\text{ A}$	—	39	—	V
			$I_{TLP} = 30\text{ A}$	—	74.5	—	
Dynamic resistance	R_{DYN}	(Note 2)	—	—	1.25	—	Ω
Total capacitance	C_t	(Note 3)	$V_R = 0\text{ V}$, $f = 1\text{ MHz}$	—	9.5	—	pF

Note 1: Based on IEC61000-4-5 8/20 μs pulse.

Note 2: TLP parameter: $Z_0 = 50\ \Omega$, $t_p = 100\text{ ns}$, $t_r = 300\text{ ps}$, averaging window: $t = 30\text{ ns}$ to 60 ns , extraction of dynamic resistance using a least-squares fit of TLP characteristics at I_{PP} between 8 A to 16 A .

Note 3: Guaranteed by design.

5. Marking

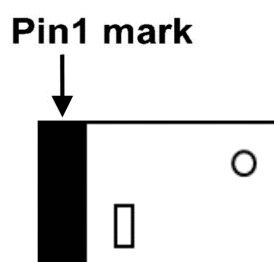


Fig. 5.1 Marking

6. Land Pattern Dimensions (for reference only)

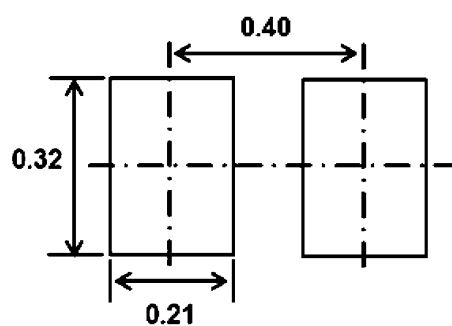


Fig. 6.1 Land Pattern Dimensions (Unit: mm)

7. Characteristics Curves (Note)

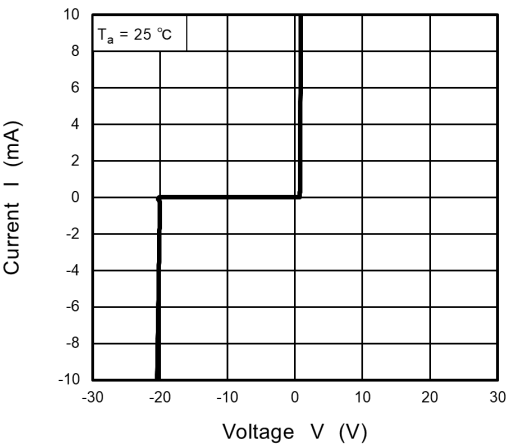


Fig. 7.1 I - V

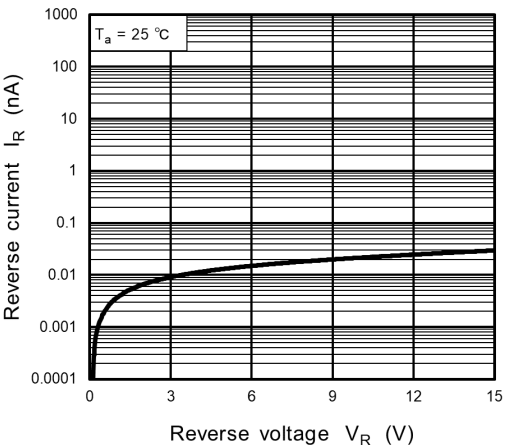


Fig. 7.2 I_R - V_R

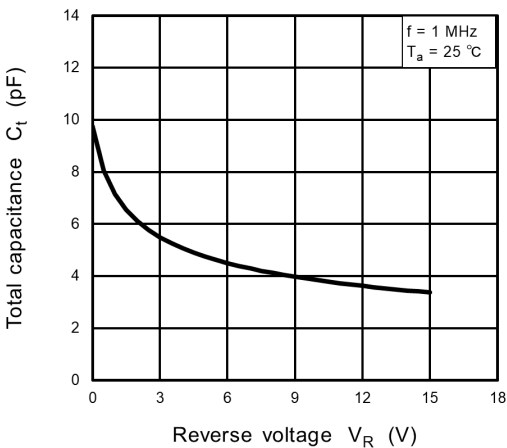


Fig. 7.3 C_t - V_R

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

8. Clamp Voltage - Peak Pulse Current (V_C - I_{PP}) (Note)

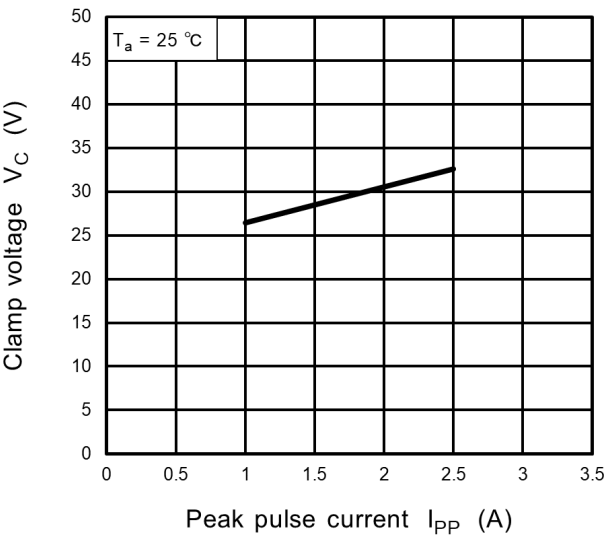


Fig. 8.1 V_C - I_{PP}

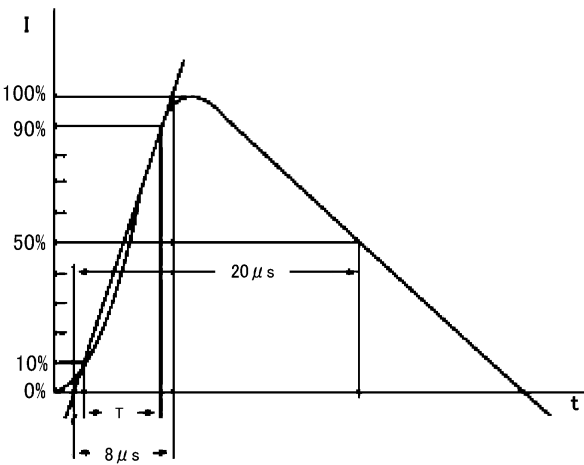


Fig. 8.2 Based on IEC61000-4-5 8/20 μs pulse.(Ed.2)

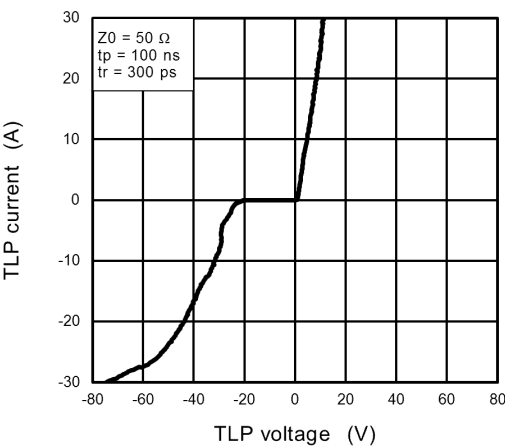


Fig. 8.3 TLP

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

9. ESD Clamp Waveform (Note)

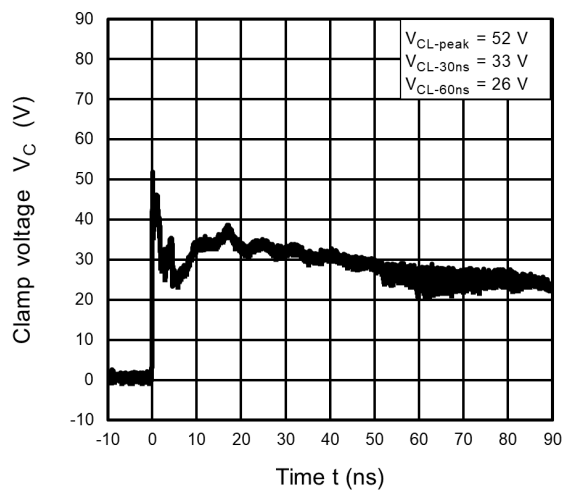


Fig. 9.1 +8 kV

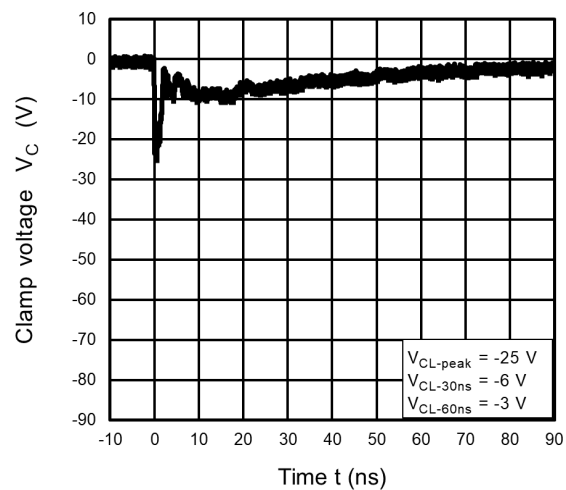


Fig. 9.2 -8 kV

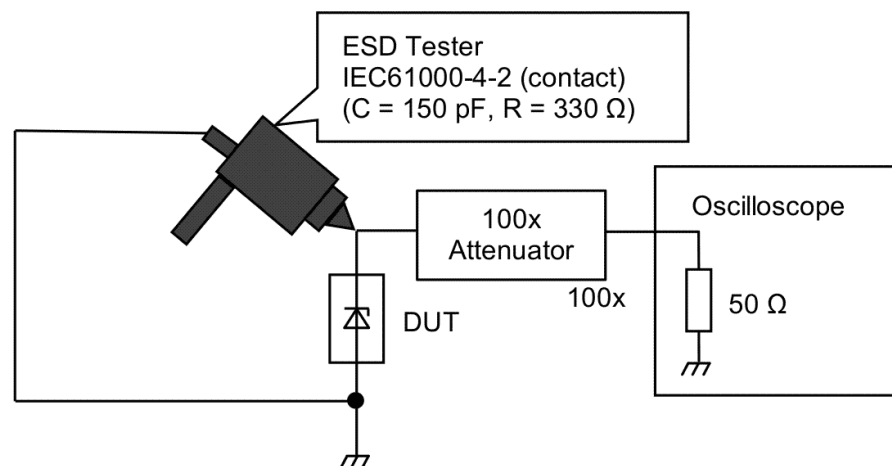
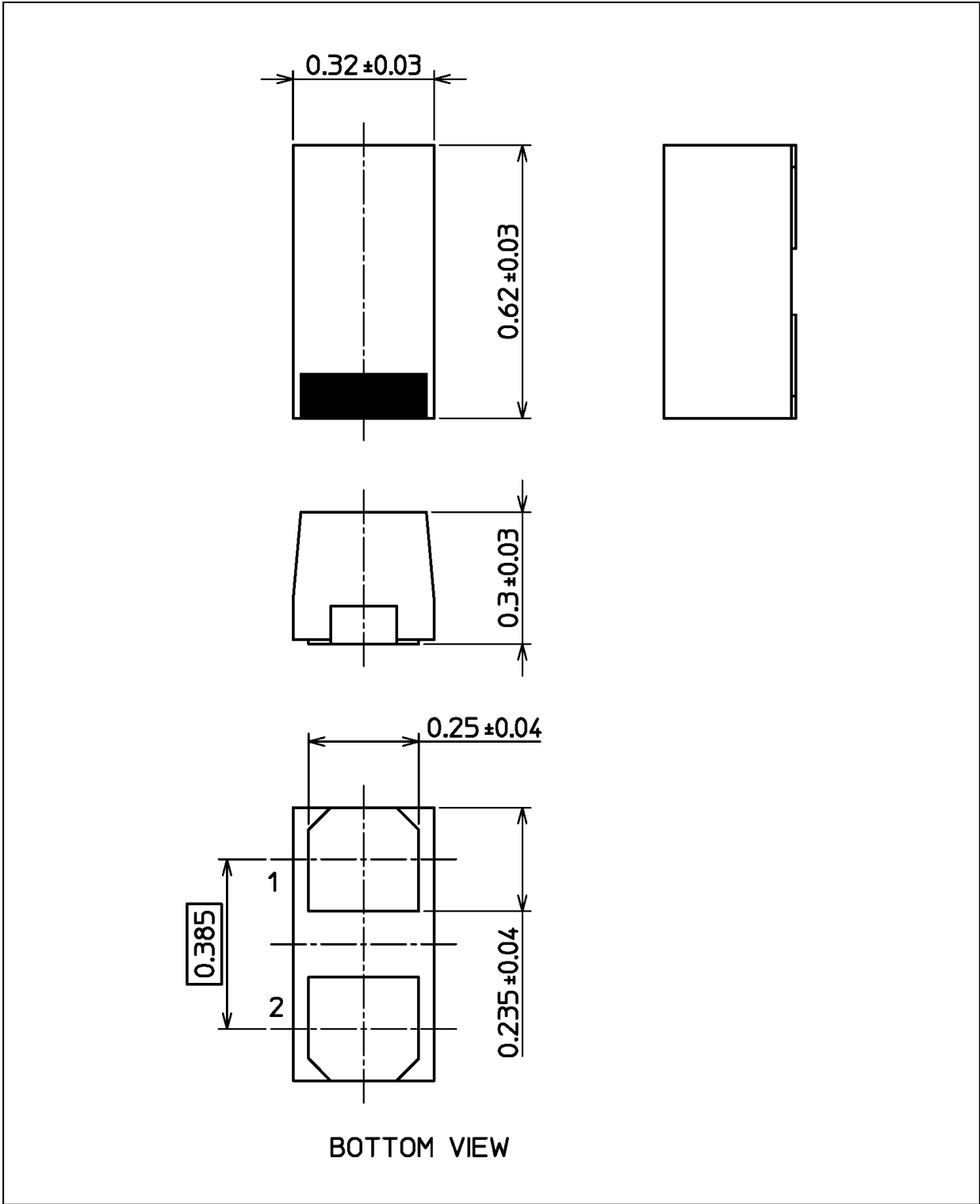


Fig. 9.3 IEC61000-4-2 (Contact)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Package Dimensions

Unit: mm



Weight: 0.2 mg (typ.)

Package Name(s)
Nickname: SL2

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